

AMENDMENTS TO THE SPECIFICATION:

Please insert the following paragraph starting at page 27, after line 23:

FIG. 53 is a cross-sectional view along the extending direction of the conductor patterns of the semiconductor device according to the second embodiment of the present invention, which shows a structure thereof.

Please amend the paragraph starting at page 38, line 22, as follows:

Then, a silicon oxide film is deposited on the entire surface by, e.g., CVD method, and then etched to form the sidewall insulation film 32 on the side walls of the interlayer insulation film 28 (FIG. 53) and the side walls of the laminated film of the gate electrodes 20, the insulation film 36 and the etching stopper film 22 (FIG. 6B).